







Trento Meeting 2018 Munich

Silicon Sensors of the CMS High Granularity Calorimeter

Thomas Bergauer On behalf the CMS collaboration

20 Feb 2018



CMS Phase-II Upgrade



- CMS Phase 2 upgrade during LS-3 (around 2024-2026) for HL-LHC Phase
 - 5-7 times higher instantaneous luminosity
 - 10x integrated luminosity (3000 fb⁻¹)
- A major challenge for detector design
 - New tracker, trigger, muon and calorimeters







CMS Endcap Calorimeter



Current CMS Calorimeters:

- Designed for integrated luminosity of maximal 500 fb⁻¹
- Electromagnetic: PbWO₄ crystals
- Hadronic: plastic scintillators

Environment of CMS Endcap at HL-LHC:

- Fluences of up to 10¹⁶ n_{eq}/cm²
- doses of up to 1.5 MGy
- Pile-up of up to 200 collisions/crossing
- \rightarrow Only silicon detectors are
 - radiation tolerant enough
 - Fast enough to mitigate pile-ups
 - Fine segmented to allow high granularity
 - affordable







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CMS is planning to build a High Granularity Calorimeter for Phase-II at HL-LHC

- Covering 1.5 < η < 3.0
- Features unprecedented transverse and longitudinal segmentation
 - Silicon in high radiation areas
 - Scintillating tiles in the low-radiation region of CE-H (Mixed Silicon-Scintillator cassettes)





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Scintillators



CMS High Granularity Calorimeter



	CE-E	CE-H (Si)	CE-H (Si + Scint)				
Active	Silicon	sensors	Scintillators				
Absorber	Lead	Stainless steel					
Depth	26X ₀ / 1.7λ	9λ					
Layers	28	8	16				
Weight	23t	205t					



	Silicon sensors	Scintillators
Area	600 m ²	500 m ²
# Modules	25,000	2500
Channels Size	0.5-1 cm ²	4-30 cm ²
# Channels	6 Mio	400k
Op. temperature	-30° C	-30° C



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Si Detector Modules

Silicon detector module is of hexagonal shape and is a stack of:

- PCB: "hexaboard": contains FE ASICs and connects to Si sensor via wirebonds through holes
- Hexagonal Si-Sensor
- Kapton sheet for HV isolation
- Copper/Tungsten Base plate

The whole module sits on a copper cooling plate with CO₂ cooling channels

Additional components:

- 2nd PCB (not shown): Motherboard for powering, data concentration, trigger generation and bi-directional communication
- Trigger/data transfer: low-power GBT links (lpGBT)

Current FE chip prototype is called HGROCv1, *submitted in July 2017, recently received*

- Based on SKIROC of CALICE
- 32 channels (final version -> 72+2+4)
- Dual polarity (p-type and n-type sensors)
- Low noise: 2000 e⁻ @ 50pF
- Dark current compensation
 - DAC is sinking up 20 µA (channel wise)
 - Input protection diodes limiting input voltage to <1V: sinking mA

"Three chips in one":

- ADC: Charge 0–100 fC [11 bits]
- Time over Threshold: 0.1–10 pC [12 bits]
- Time of Arrival with 25 ps resolution > 50 fC [12 bits]

Hexagonal Silicon Sensors

- Hexagonal sensor geometry as largest tileable polygon
 - maximize use of circular wafer
 - Minimize ratio of periphery to surface area
 - Truncated tips ("mouse-bites") used for module mounting → Further increase use of wafer surface
- Each sensor consists of individual pads (cells)
- Three thicknesses based on radiation and occupancy considerations

Thickness [µm]	# cells	Cell size [cm²]	Cell C [pF]	Bulk polarity	Expected Fluence [E15 n cm ⁻²]	# wafers (8 inch)	# partial 8 inch wafers
300	192	1.18	45	p (n)	0.1-0.5	13164	1284
200	192	1.18	65	р	0.5-2.5	8712	144
120	432	0.52	50	р	2-7	3000	324
					Total:	24876	1752

Radiation Hardness

- Fluence is n-dominated w.r.t. charged hadrons (90%/10%)
- Deployment of thinner sensors in the higher fluence regions of the calorimeter
 - improved charge collection
 - reduced leakage current
- Typical signals in calorimeter much higher than MIPs
 - MIP sensitivity needed for energy calibration (e.g. isolated muons)

Radiation Hardness

Radiation hardness study performed on different materials

- Deep-diffused FZ and Epitaxial of different thicknesses
- Need to operate at -30° C to keep dark ۲ current below limit given by power supplies (10mA)
- N-type sensors would give 20% more signal, but....

dd-FZ 200µm

Fluence, n/cm²

P- type@600V Thickness [µm]	Signal for MIP before Irrad. [ke ⁻]	Signal for MIP after irrad [ke ⁻]
300 dd-FZ	22	10
200 dd-FZ	15	6
120 epi	9	5

 10^{-4}

ddFZ 320µm

10¹⁵

10¹⁶

Feasibility of n-type FZ material

- Studies of CMS Tracker revealed non-Gaussian noise caused by micro-discharges due to high electric field
 - CCE after irradiation similar to p-type
- TCAD Study performed to study electric field of n-type vs. p-type sensors (for two different pstop designs)
 - Electric fields in N-type is higher than the corresponding P-type ones
 - Higher Pad distance leads to higher electric field peaks (for all types)
- Biggest advantage of n-type: 20-30% cost saving

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Testbeams with 6" sensors

Beam tests at FNAL and CERN performed with modules built on TP geometry (6" sensors) to study

- Longitudinal and transverse shower shapes
- Energy, position, time resolution
- Achieved resolution for:
 - Energy: below ~7%, for e energy > 50 GeV
 - Position: below ~ 2mm, for e energy > 50 GeV
 - Time: ~ 20 ps

6" vs. 8" sensors

- HGCal Technical Proposal (TP) was based on 6 inch sensors (2015)
- Recent advancements allowed us to define 8inch sensors as baseline for Technical Design Report (TDR) submitted at the end of 2017
- Advantages of larger sensors:
 - Simplifies module mechanics by larger sensors/modules
 - Affordable only if maximal wafer area is used
- Disadvantages:
 - Precision of full-mask photolithography a bit worse than for 6" (no standard procedure)
 - Deep diffused Float zone wafer material is not available on 8-inch

- Hamamatsu (HPK) was the only one highquality high-volume producer for 6" sensors
 - They are well advanced in porting this technology to 8" production lines
 - Two demonstrator batches on 8" produced
- HEPHY Vienna is working with Infineon (IFX) to establish them as vendor for HEP Sensors
 - 6" (n/p-type) and 8" (p-type) production performed for the CMS tracker
 - HGC sensor prototypes in 8" p-type
- US-Grant to Novati/Tezzaron/Nhanced to develop HEP sensors on 8 inches

First HPK 8-inch p-Type HGC Sensors

R&D with producers

HPK used stepper technology for first "demonstrator" run on 8-inch

- Small masks used to consecutively expose small squares on wafer,
- results in excellent lithography (sub-µm structures)
- Some disadvantages: no pad numbers, limitations in layout
- First batch:
 - Different process splits to evaluate best parameters
 - Reason for defective cells thought to be understood by HPK
- Stepper technique will not be used for mass production
 - Full-wafer lithography equipment for 8 inches currently being purchased by HPK
 - First delivery of real 8" prototypes in Q2/2018

1st batch:

Sensor development with Infineon

R&D with producers

- We are collaborating with them since a couple of years to develop Si sensors for HEP
 - 2012-2014: production of 6" p-on-n sensors
 - 2015-2017: production of first Si strip sensors on 8-inch FZ ptype wafers
 - 2016/17 onwards: production of Si pad sensors for HGCal
- Quality constantly improving
 - One remaining problem: premature IV breakdowns, scaling with sensor size
 - Addressed now by thicker backside implantation

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Sensor Characterization

- Sensor is a bunch of parallel diodes without any biasing structure
- Simple IV measurements show influence of leaky cell to neighbors
- Only 7-needle measurements give precise results (only if neighbor cells are not in breakdown)

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Contacting all cells in Parallel: Full Probe card

- Switching & Probe cards allow testing each pad while other pads are biased
- Flexible design: can be adapted to different sizes and geometries
 - "upper" switching card houses multiplexers and microprocessor
 - "lower" probe cards equipped with "pogo-pins" (spring loaded contacts) to match actual sensor geometry

 Will allow also coupling to readout (e.g. to test noise of irradiated sensors)

IFX 8"

Sensor Characterization

Performance of Switching/Probe card system

- Testing procedure:
 - IV curve: 11 voltage steps up to 1000V
 - CV curve: 15 voltage steps up to 300V
 Performed for all cells for each voltage step, then voltage is ramped to next step
- Probe card has been used to characterize ~90 HPK sensors for test beams
- Complicated network of parasitic impedances
 - Need open, short AND load correction of LCR meter to obtain an almost correct CV curve
 - We are working on better CV measurement to precisely determine active thickness

Sensor Layout Optimization

- Inter-cell gap is main parameter for design optimization
- Studied by TCAD simulations and measurements
 - Prototype sensors equipped with 4 quadrants of different pad distance (20, 40, 60, 80 µm) and p-stop geometry (atoll vs. common)
- Results: higher breakdown voltage for smaller pad distance
 - In contradiction to inter-pad isolation performance and capacitances (better for larger distances)

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- High Granularity Calorimeter (HGCal) is the upgrade of the endcap calorimeters of CMS
 - Based on prior work of CALICE and SiD/ILC
 - Consists of silicon sensors and scintillators as active elements
- Will be the largest Si-based particle detector by factor of three (600 m² active silicon area)
 - Move to 8-inch sensors is a significant cost saving and complexity reduction
 - Planar 300µm and 200µm thick sensors, epitaxial 120µm
 - Three vendors potentially capable of production: Hamamatsu, Infineon, Novati
- Basic design of the detector has been validated
 - Must be shown for 8-inch technology as well, despite tight timescale

Year Long Shutdowns	2016		2017		2018		2019	LS2	2020		2021		2022		2023		2024	i	2025 LS3	i	2026
Endcap Calorimeters	Des	ign - R&	D - Demo.	TDR	Prototyping/ Enginee	ering			EDR	Prepro	oduction/Productio	n/Ass n/Ass	embly Calı embly	rimeter Calrim	Endcap 1 neter Er	ndcap 2	Flo	at /Ins	tallation /Com Float /Commis	i nissioni ssioning	ing J

THE END

Various slides follow

Testbeams with 6" sensors

Aim to test full EE+FH+BH - like setup BH ~ O AHCAL FH EE

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 A geometry which repeats the hexagonal cell pitch across modules is used

 optimized for trigger cell geometry

Layout Optimization

Periphery Simulation

- Synopsis TCAD 2D
- Dimensions between edge implant, floating and grounded guard ring varied
- It turned out that "old" design was already very good

HGC Periphery (µm)	Edge- Width	Edge- MO	Edge- Guard	Guard- MO left	Guard- Width	Guard- MO right	Guard- Bias	Bias- MO	Bias- Width
IFX_V1	502	50	119.5	32.5	18	12.5	17	22.5	131.5
New Geo	400	50	119.5	40	18	10	24.5	10	131.5

Simplifying testing at vendors

- proposing layout for small "probe cards" to allow 7-needle testing
- Even for edge and border cells
- Need to have "landing pads" in otherwise unused region of wafer

Hexaboard probe card

Purpose: Signal/Noise tests of bare (irradiated) sensors without the need of module assembly of irradiated sensors or irradiation of whole module

- Aim: understand noise behavior of irradiated sensors (n-type/p-type)
- Replace wire-bonds by pogo pins
- Added holes for laser on cell center and inter-cell regions
- Status: Design finished, should be ready in ~2 months from now
- To be installed in CERN probe station
- Possible collaboration of new "system test" group with sensors group

Details on Sensor Variants

CE-E: ECAL

Active thickness (μ m)	300	200	120
Area (m ²)	245	181	72
Largest lifetime dose (Mrad)	3	20	100
Largest lifetime fluence (n_{eq}/cm^2)	0.5×10^{15}	2.5×10^{15}	7×10 ¹⁵
Largest outer radius (cm)	\approx 180	≈100	≈70
Smallest inner radius (cm)	≈ 100	≈70	≈35
Cell size (cm ²)	1.18	1.18	0.52
Initial S/N for MIP	11	6	4.5
Smallest $S/N(MIP)$ after 3000 fb ⁻¹	4.7	2.3	2.2

CE-H: HCAL

• - · · · • • · · -	Scintillator	Si	Si
Sensor thickness	3 mm	300 µm	$200 \mu m$
Area (m ²)	480	71	15
Largest lifetime dose (Mrad)	<0.3	30	100
Largest lifetime fluence (n_{eq}/cm^2)	8×10 ¹³	5×10 ¹⁴	2.5×10^{15}
Largest outer radius (cm)	≈235	≈160	≈100
Smallest inner radius (cm)	≈90	≈ 80	≈45
Cell size (cm ²)	2×2 to	1.18	1.18
	5.5×5.5		
Initial S/N for a MIP	≫5	11	6
Smallest $S/N(MIP)$ after 3000 fb ⁻¹	5	4.7	2.3

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FE ASIC History

- SKIROC2: ASIC used by CALICE in the SiW ECAL
 - Dedicated 64 channel Si-detector readout ASIC, SiGe 350 nm
- SKIROC2cms: submitted and received in Q1/2016
 - Modification for test beams with CMS-like running conditions
 - 40 MHz clock and sampling, Gain + ToA + ToT
- Test Vehicle 1: *submitted in May 2016, received in August 2016*
 - First HGCROC test vehicle in CMOS 130 nm architecture
 - Dedicated to preamplifier studies
- Test Vehicle 2: *submitted in December 2016, received in May 2017*
 - Dedicated to analog channel study for TDR
- HGCROCv1: submitted in July 2017, recently received
 - All analog and mixed blocks; many simplified digital blocks

➡ Final HGCROC submission by mid 2019!

72 (+2 +4) channels, i.e. 3/6 chips per sensor

Automated Module Assembly

- 6"modules
 - 6 pick-up tools for PCBs, 6 for Sensors
 - 2 Portable assembly trays
 - 2 Portable component staging trays
- Enables 12 glue steps per day
 - Complete 6 modules/day, Start 6 others to be finished the next day
 - Kapton preassembly rate 6/day

Switchcard Schematics

6" Irradiation @ Ljubljana

Triga Mark III reactor at JSI Ljubljana recently upgraded for irradiation of large objects

- Funding by AIDA-2020
- 6" HPK sensors just fit (verified)
- Fluences: 1E14, 5E14 and 1E15 (further steps to be negotiated)
- Sensor should have some protection (plastic bag, thin box) and fixed to this plate
- Can be shipped there anytime, returned 4-6 weeks later
- Need to agree on samples, e.g.
 - 3 pcs. n-type
 - 3 pcs. p-type (atoll)
 - 3 pcs. p-type (common)

(all 300um thickness)

Mounting plate (135 mm x 300 mm)

Irradiation channel

17 Oct 2017

T. Bergauer

8" Irradiations @ US

Setups:

- Rhode Island reactor (RINSC)
 - close to Brown Univ.
 - Foil dosimetry for spectrum determination
 - 6/8 inches beam port
 - Annealing study performed
- FSU protons (Tandem Van-der-Graaf)
 - Diode samples irradiated
 - Samples tested in dark box (no probe station?)
- Texas Tech: IV/CV
 - IV/CV performed on cold chuck

